ESP32-WROVER-B & ESP32-WROVER-IB





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About This Document

This document provides the specifications for the ESP32-WROVER-B and ESP32-WROVER-IB modules.

Document Updates

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Revision History

For revision history of this document, please refer to the last page.

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1 Overview

ESP32-WROVER-B and ESP32-WROVER-IB are two powerful, generic Wi-Fi + Bluetooth[®] + Bluetooth LE MCU modules that target a wide variety of applications, ranging from low-power sensor networks to the most demanding tasks, such as voice encoding, music streaming and MP3 decoding.

ESP32-WROVER-B comes with a PCB antenna, and ESP32-WROVER-IB with an external antenna connector. The information in this datasheet is applicable to both modules.

Both module series offers a wide selection of variants for customers as shown in Table 1 and 2.

Ordering Code	Flash ²	PSRAM	Ambient Temp. ³ (°C)	Size ⁴ (mm)
ESP32-WROVER-B-N4R8	4 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	
ESP32-WROVER-B-N8R8	8 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	18.0 x 31.4 x 3.3
ESP32-WROVER-B-N16R8	16 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	

Table 1: ESP32-WROVER-B Series Comparison¹

¹ This table shares the same notes presented in the table 2 below.

Table 2: ESP32-WROVER-IB Series Comparison

Ordering Code	Flash ²	PSRAM	Ambient Temp. ³ (°C)	Size ⁴ (mm)
ESP32-WROVER-IB-N4R8	4 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	
ESP32-WROVER-IB-N8R8	8 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	18.0 x 31.4 x 3.3
ESP32-WROVER-IB-N16R8	16 MB (Quad SPI)	8 MB (Quad SPI)	-40 ~ 85	

² The integrated flash supports:

- More than 100,000 program/erase cycles

- More than 20 years data retention time

³ Ambient temperature specifies the recommended temperature range of the environment immediately outside the Espressif module.

⁴ For details, refer to Section 8 *Physical Dimensions*.

At the core of the module is the ESP32-DOWD chip*.

Note:

- For details on the part numbers of the ESP32 family of chips, please refer to the document ESP32 Datasheet.
- For chip revision identification, ESP-IDF release that supports a specific chip revision, and other information on chip revisions, please refer to <u>ESP32 Series SoC Errata</u> > Section <u>Chip Revision Identification</u>.

Table 3 provides the specifications of ESP32-WROVER-B and ESP32-WROVER-IB.

Categories	Items	Specifications				
	RF certification	See certificates for <u>ESP32-WROVER-B</u> and				
Certification	Ki Certification	ESP32-WROVER-IB				
Certification	Bluetooth certification	BQB				
	Green certification	Rohs, Reach				
Test	Reliablity	HTOL/HTSL/uHAST/TCT/ESD				
		802.11 b/g/n (802.11n up to 150 Mbps)				
Wi-Fi	Protocols	A-MPDU and A-MSDU aggregation and 0.4 μ s guard in-				
VVI-FI		terval support				
	Center frequency range of op-	2412 ~ 2484 MHz				
	erating channel					
	Protocols	Bluetooth v4.2 BR/EDR and Bluetooth LE specification				
		NZIF receiver with –97 dBm sensitivity				
Bluetooth	Radio	Class-1, class-2 and class-3 transmitter				
		AFH				
	Audio CVSD and SBC					
		SD card, UART, SPI, SDIO, I2C, LED PWM, Motor PWM,				
	Module interfaces	I2S, IR, pulse counter, GPIO, capacitive touch sensor,				
		ADC, DAC, TWAI [®] (compatible with ISO 11898-1, i.e. CAN				
		Specification 2.0)				
	Integrated crystal	40 MHz crystal				
	Integrated SPI flash	See Table 1 and 2				
Hardware	Integrated PSRAM	See Table 1 and 2				
ThatGivare	Operating voltage/Power sup-	3.0 V ~ 3.6 V				
	ply					
	Minimum current delivered by	500 mA				
	power supply					
	Recommended operating am-	-40 °C ~ 85 °C				
	bient temperature range					
	Package size	18 mm × 31.4 mm × 3.3 mm				
	Moisture sensitivity level (MSL)	SL) Level 3				

Table 3: ESP32-WROVER-B & ESP32-WROVER-IB Specifications

2 Pin Definitions

2.1 Pin Layout





2.2 Pin Description

ESP32-WROVER-B and ESP32-WROVER-IB each has 38 pins. See pin definitions in Table 4.

Table 4: Pin Definitions

Name	No.	Туре	Function
GND	1	Ρ	Ground
3V3	2	Ρ	Power supply

Name No. Type		Туре	Function			
EN 3 I Module-		1	lule-enable signal. Active high.			
SENSOR_VP	4		GPI036, ADC1_CHO, RTC_GPI00			
SENSOR_VN	5		GPIO39, ADC1_CH3, RTC_GPIO3			
1034	6		GPIO34, ADC1_CH6, RTC_GPIO4			
1035	7		GPIO35, ADC1_CH7, RTC_GPIO5			
1000			GPIO32, XTAL_32K_P (32.768 kHz crystal oscillator input), ADC1_CH4,			
1032	8	1/0	TOUCH9, RTC_GPIO9			
1000			GPIO33, XTAL_32K_N (32.768 kHz crystal oscillator output),			
1033	9	1/0	ADC1_CH5, TOUCH8, RTC_GPI08			
1025	10	I/O	GPI025, DAC_1, ADC2_CH8, RTC_GPI06, EMAC_RXD0			
1026	11	1/0	GPIO26, DAC_2, ADC2_CH9, RTC_GPIO7, EMAC_RXD1			
1027	12	1/0	GPI027, ADC2_CH7, TOUCH7, RTC_GPI017, EMAC_RX_DV			
			GPI014, ADC2_CH6, TOUCH6, RTC_GPI016, MTMS, HSPICLK,			
1014	13	1/0	HS2_CLK, SD_CLK, EMAC_TXD2			
			GPI012, ADC2_CH5, TOUCH5, RTC_GPI015, MTDI, HSPIQ, HS2_DATA2,			
1012	14	1/0	SD_DATA2, EMAC_TXD3			
GND	15	P	Ground			
			GPI013, ADC2_CH4, TOUCH4, RTC_GPI014, MTCK, HSPID, HS2_DATA3,			
1013	16	1/0	SD_DATA3, EMAC_RX_ER			
SHD/SD2*	17	1/0	GPIO9, SD_DATA2, SPIHD, HS1_DATA2, U1RXD			
SWP/SD3*	18	1/0	GPIO10, SD_DATA3, SPIWP, HS1_DATA3, U1TXD			
SCS/CMD*	19	1/0	GPI011, SD_CMD, SPICSO, HS1_CMD, U1RTS			
SCK/CLK*	20	1/0	GPIO6, SD_CLK, SPICLK, HS1_CLK, U1CTS			
SDO/SDO*	21	1/0	GPIO7, SD_DATAO, SPIQ, HS1_DATAO, U2RTS			
SDI/SD1*	22	1/0	GPIO8, SD_DATA1, SPID, HS1_DATA1, U2CTS			
1045			GPI015, ADC2_CH3, TOUCH3, MTDO, HSPICSO, RTC_GPI013,			
1015	23	1/0	HS2_CMD, SD_CMD, EMAC_RXD3			
100	0.1		GPIO2, ADC2_CH2, TOUCH2, RTC_GPIO12, HSPIWP, HS2_DATAO,			
102	24	1/0	SD_DATAO			
100	25	I/O	GPIOO, ADC2_CH1, TOUCH1, RTC_GPIO11, CLK_OUT1, EMAC_TX_CLK			
10.4		1/0	GPIO4, ADC2_CHO, TOUCHO, RTC_GPIO10, HSPIHD, HS2_DATA1,			
104	26	1/0	SD_DATA1, EMAC_TX_ER			
NC1	27	-	-			
NC2	28	-	-			
105	29	1/0	GPIO5, VSPICSO, HS1_DATA6, EMAC_RX_CLK			
1018	30	1/0	GPIO18, VSPICLK, HS1_DATA7			
1019	31	1/0	GPI019, VSPIQ, UOCTS, EMAC_TXDO			
NC	32	-	-			
1021	33	I/O	GPIO21, VSPIHD, EMAC_TX_EN			
RXDO	34	1/0	GPIO3, UORXD, CLK_OUT2			
TXDO	35	1/0	GPIO1, UOTXD, CLK_OUT3, EMAC_RXD2			
1022	36	1/0	GPIO22, VSPIWP, UORTS, EMAC_TXD1			
1023	37	1/0	GPIO23, VSPID, HS1_STROBE			

Name	No.	Туре	Function
GND	38	Ρ	Ground

Notice:

* Pins SCK/CLK, SDO/SDO, SDI/SD1, SHD/SD2, SWP/SD3 and SCS/CMD, namely, GPIO6 to GPIO11 are connected to the SPI flash integrated on the module and are not recommended for other uses.

2.3 Strapping Pins

ESP32 has five strapping pins, which can be seen in Chapter 6 Schematics:

- MTDI
- GPI00
- GPI02
- MTDO
- GPI05

Software can read the values of these five bits from register "GPIO_STRAPPING".

During the chip's system reset release (power-on-reset, RTC watchdog reset and brownout reset), the latches of the strapping pins sample the voltage level as strapping bits of "0" or "1", and hold these bits until the chip is powered down or shut down. The strapping bits configure the device's boot mode, the operating voltage of VDD_SDIO and other initial system settings.

Each strapping pin is connected to its internal pull-up/pull-down during the chip reset. Consequently, if a strapping pin is unconnected or the connected external circuit is high-impedance, the internal weak pull-up/pull-down will determine the default input level of the strapping pins.

To change the strapping bit values, users can apply the external pull-down/pull-up resistances, or use the host MCU's GPIOs to control the voltage level of these pins when powering on ESP32.

After reset release, the strapping pins work as normal-function pins.

Refer to Table 5 for a detailed boot-mode configuration by strapping pins.

Table 5: Strapping Pins

Voltage of Internal LDO (VDD_SDIO)								
Pin Default		3.3 V	1.8 V					
MTDI	Pull-down	0	1					
	Booting Mode							
Pin Default		SPI Boot	Download Boot					
GPIOO	Pull-up	1	0					
GPIO2	Pull-down	Don't-care	0					
Enabling/Disabling Debugging Log Print over UOTXD During Booting								
Pin	Pin Default UOTXD Active		UOTXD Silent					
MTDO Pull-up		1	0					

Not Recommended For New Designs (NRND)

Timing of SDIO Slave									
FE Sampling FE Sampling RE Sampling RE Sampling									
Pin	Default	FE Output	RE Output	FE Output	RE Output				
MTDO	Pull-up	0	0	1	1				
GPIO5 Pull-up		0	1	0	1				

Note:

- Firmware can configure register bits to change the settings of "Voltage of Internal LDO (VDD_SDIO)" and "Timing of SDIO Slave" after booting.
- Internal pull-up resistor (R9) for MTDI is not populated in the module, as the flash and SRAM in ESP32-WROVER-B and ESP32-WROVER-IB only support a power voltage of 3.3 V (output by VDD_SDIO).

The illustration below shows the setup and hold times for the strapping pins before and after the CHIP_PU signal goes high. Details about the parameters are listed in Table 6.



Figure 2: Setup and Hold Times for the Strapping Pins

Parameters	Description	Min	Unit
t ₀	Setup time before CHIP_PU goes from low to high	0	ms
t ₁	Hold time after CHIP_PU goes high	1	ms

3 Functional Description

This chapter describes the modules and functions integrated in ESP32-WROVER-B and ESP32-WROVER-IB.

3.1 CPU and Internal Memory

ESP32-DOWD contains two low-power Xtensa® 32-bit LX6 microprocessors. The internal memory includes:

- 448 KB of ROM for booting and core functions.
- 520 KB of on-chip SRAM for data and instructions.
- 8 KB of SRAM in RTC, which is called RTC FAST Memory and can be used for data storage; it is accessed by the main CPU during RTC Boot from the Deep-sleep mode.
- 8 KB of SRAM in RTC, which is called RTC SLOW Memory and can be accessed by the co-processor during the Deep-sleep mode.
- 1 Kbit of eFuse: 256 bits are used for the system (MAC address and chip configuration) and the remaining 768 bits are reserved for customer applications, including flash-encryption and chip-ID.

3.2 External Flash and SRAM

ESP32 supports multiple external QSPI flash and SRAM chips. More details can be found in Chapter SPI in the *ESP32 Technical Reference Manual*. ESP32 also supports hardware encryption/decryption based on AES to protect developers' programs and data in flash.

ESP32 can access the external QSPI flash and SRAM through high-speed caches.

- The external flash can be mapped into CPU instruction memory space and read-only memory space simultaneously.
 - When external flash is mapped into CPU instruction memory space, up to 11 MB + 248 KB can be mapped at a time. Note that if more than 3 MB + 248 KB are mapped, cache performance will be reduced due to speculative reads by the CPU.
 - When external flash is mapped into read-only data memory space, up to 4 MB can be mapped at a time. 8-bit, 16-bit and 32-bit reads are supported.
- External SRAM can be mapped into CPU data memory space. Up to 4 MB can be mapped at a time. 8-bit, 16-bit and 32-bit reads and writes are supported.

ESP32-WROVER-B and ESP32-WROVER-IB integrate a 4 MB SPI flash and an 8 MB PSRAM for more memory space.

3.3 Crystal Oscillators

The module uses a 40-MHz crystal oscillator.

3.4 RTC and Low-Power Management

With the use of advanced power-management technologies, ESP32 can switch between different power modes.

For details on ESP32's power consumption in different power modes, please refer to section "RTC and Low-Power Management" in *ESP32 Datasheet*.

4 Peripherals and Sensors

Please refer to Section Peripherals and Sensors in ESP32 Datasheet.

Note:

External connections can be made to any GPIO except for GPIOs in the range 6-11, 16, or 17. GPIOs 6-11 are connected to the module's integrated SPI flash and PSRAM. GPIOs 16 and 17 are connected to the module's integrated PSRAM. For details, please see Section 6 Schematics.

Electrical Characteristics 5

Absolute Maximum Ratings 5.1

Stresses beyond the absolute maximum ratings listed in the table below may cause permanent damage to the device. These are stress ratings only, and do not refer to the functional operation of the device that should follow the recommended operating conditions.

Table	7: Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
VDD33	Power supply voltage	-0.3	3.6	V
_{output} ¹	Cumulative IO output current	-	1,100	mA
T _{store}	Storage temperature	-40	105	°C

^{1.} The module worked properly after a 24-hour test in ambient temperature at 25 °C, and the IOs in three domains (VDD3P3_RTC, VDD3P3_CPU, VDD_SDIO) output high logic level to ground. Please note that pins occupied by flash and/or PSRAM in the VDD_SDIO power domain were excluded from the test.

2. Please see Appendix IO_MUX in ESP32 Datasheet for IO's power domain.

Recommended Operating Conditions 5.2

Table 8: Recommended Operating Conditions

Symbol	Parameter		Typical	Max	Unit
VDD33	Power supply voltage	3.0	3.3	3.6	V
$ _{VDD}$	Current delivered by external power supply		-	-	А
Т	Operating ambient temperature		-	85	°C

5.3 DC Characteristics (3.3 V, 25 °C)

Table 9: DC Characteristics (3.3 V, 25 °C)

Symbol	Par	Min	Тур	Max	Unit	
C _{IN}	Pin capacitance		-	2	-	рF
V_{IH}	High-level input voltage		$0.75 \times VDD^1$	-	VDD1+0.3	V
V_{IL}	Low-level input voltage		-0.3	-	$0.25 \times VDD^1$	V
$ _{IH}$	High-level input current	-	-	50	nA	
$ _{IL}$	Low-level input current	-	-	50	nA	
V_{OH}	High-level output voltage	$0.8 \times VDD^1$	-	-	V	
V_{OL}	Low-level output voltage		-	-	0.1×VDD ¹	V
	High-level source current	High-level source current VDD3P3_CPU power domain ^{1, 2}		40	-	mA
	(VDD ¹ = 3.3 V, V _{OH} >= 2.64 V,	VDD3P3_RTC power domain ^{1, 2}	-	40	-	mA
OH	output drive strength set to	VDD_SDIO power domain ^{1, 3}	-	20	-	mA
	the maximum)	-				

Symbol	Parameter	Min	Тур	Max	Unit	
	Low-level sink current					
I_{OL}	(VDD ¹ = 3.3 V, V _{OL} = 0.495 V,	-	28	-	mA	
	output drive strength set to the maximum)					
R_{PU}	Resistance of internal pull-up resistor	-	45	-	kΩ	
R_{PD}	Resistance of internal pull-down resistor	-	45	-	kΩ	
V_{IL_nRST}	Low-level input voltage of CHIP_PU to shut down the chip	-	-	0.6	V	

Notes:

- 1. Please see Appendix *IO_MUX* in <u>ESP32 Datasheet</u> for IO's power domain. VDD is the I/O voltage for a particular power domain of pins.
- 2. For VDD3P3_CPU and VDD3P3_RTC power domain, per-pin current sourced in the same domain is gradually reduced from around 40 mA to around 29 mA, V_{OH}>=2.64 V, as the number of current-source pins increases.
- 3. Pins occupied by flash and/or PSRAM in the VDD_SDIO power domain were excluded from the test.

5.4 Wi-Fi Radio

Parameter	Condition	Min	Typical	Max	Unit
Center frequency range of oper-	-	2412	-	2484	MHz
ating channel note1					
Output impedance note2	-	-	*	-	Ω
TX power note3	11n, MCS7	12	13	14	dBm
	11b mode	17.5	18.5	20	dBm
Sensitivity	11b, 1 Mbps	-	-98	-	dBm
	11b, 11 Mbps	-	-89	-	dBm
	11g, 6 Mbps	-	-92	-	dBm
	11g, 54 Mbps	-	-74	-	dBm
	11n, HT20, MCS0	-	-91	-	dBm
	11n, HT20, MCS7	-	-71	-	dBm
	11n, HT40, MCS0	-	-89	-	dBm
	11n, HT40, MCS7	-	-69	-	dBm
Adjacent channel rejection	11g, 6 Mbps	-	31	-	dB
	11g, 54 Mbps	-	14	-	dB
	11n, HT20, MCS0	-	31	-	dB
	11n, HT20, MCS7	-	13	-	dB

Table 10: Wi-Fi Radio Characteristics

1. Device should operate in the center frequency range of operating channel allocated by regional regulatory authorities. Target center frequency range of operating channel is configurable by software.

- 2. For the modules that use external antennas, the output impedance is 50 Ω . For other modules without external antennas, users do not need to concern about the output impedance.
- 3. Target TX power is configurable based on device or certification requirements.

5.5 BLE Radio

5.5.1 Receiver

Parameter	Condition	Min	Тур	Max	Unit
Sensitivity @30.8% PER	-	-	-97	-	dBm
Maximum received signal @30.8% PER	-	0	-	-	dBm
Co-channel C/I	-	-	+10	-	dB
	F = FO + 1 MHz	-	-5	-	dB
	F = FO – 1 MHz	-	-5	-	dB
Adjacent observed colocitivity C/L	F = FO + 2 MHz	-	-25	-	dB
Adjacent channel selectivity C/I	F = FO – 2 MHz	-	-35	-	dB
	F = FO + 3 MHz	-	-25	-	dB
	F = FO – 3 MHz	-	-45	-	dB
	30 MHz ~ 2000 MHz	-10	-	-	dBm
Out of hand blocking parformance	2000 MHz ~ 2400	-27	-	-	dBm
Out-of-band blocking performance	MHz				
	2500 MHz ~ 3000	-27	-	-	dBm
	MHz				
	3000 MHz ~ 12.5 GHz	-10	-	-	dBm
Intermodulation	-	-36	-	-	dBm

5.5.2 Transmitter

Parameter	Condition	Min	Тур	Max	Unit
RF transmit power	-	-	0	-	dBm
Gain control step	-	-	3	-	dB
RF power control range	-	-12	-	+9	dBm
	$F = FO \pm 2 MHz$	-	-52	-	dBm
Adjacent channel transmit power	F = FO ± 3 MHz	-	-58	-	dBm
	$F = FO \pm > 3 MHz$	-	-60	-	dBm
$\Delta f 1_{ m avg}$	-	-	-	265	kHz
$\Delta f2_{\sf max}$	-	247	-	-	kHz
$\Delta f 2_{\rm avg} / \Delta f 1_{\rm avg}$	-	-	-0.92	-	-
ICFT	-	-	-10	-	kHz
Drift rate	-	-	0.7	-	kHz/50 μ s
Drift	-	-	2	-	kHz

Table 12: Transmitter Characteristics – Bluetooth LE

6 Schematics



Figure 3: Schematics of ESP32-WROVER-B

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Figure 4: Schematics of ESP32-WROVER-IB



7 Peripheral Schematics

Figure 5: Peripheral Schematics

- Soldering Pad 39 to the ground of the base board is not a must. If you choose to solder it, please apply the correct amount of soldering paste. Too much soldering paste may increase the gap between the module and the baseboard. As a result, the adhesion between other pins and the baseboard may be poor.
- To ensure the power supply to the ESP32 chip during power-up, it is advised to add an RC delay circuit at the EN pin. The recommended setting for the RC delay circuit is usually R = 10 k Ω and C = 1 μ F. However, specific parameters should be adjusted based on the power-up timing of the module and the power-up and reset sequence timing of the chip. For ESP32's power-up and reset sequence timing diagram, please refer to Section *Power Scheme* in *ESP32 Datasheet*.
- UARTO is used to download firmware and log output. When using the AT firmware, please note that the UART GPIO is already configured (refer to <u>Hardware Connection</u>). It is recommended to use the default configuration.

8 Physical Dimensions



Figure 6: ESP32-WROVER-B Physical Dimensions



Figure 7: ESP32-WROVER-IB Physical Dimensions

For information about tape, reel, and product marking, please refer to *Espressif Module Package Information*.

Not Recommended For New Designs (NRND)

Note:

9 Recommended PCB Land Pattern

This section provides the following resources for your reference:

- Figures for recommended PCB land patterns with all the dimensions needed for PCB design. See Figure 8 Recommended PCB Land Pattern.
- Source files of recommended PCB land patterns to measure dimensions not covered in Figure 8. You can view the source files for ESP32-WROVER-B and ESP32-WROVER-IB with Autodesk Viewer.



Figure 8: Recommended PCB Land Pattern



10 Dimensions of External Antenna Connector

Figure 9: Dimensions of External Antenna Connector

11 Product Handling

11.1 Storage Conditions

The products sealed in moisture barrier bags (MBB) should be stored in a non-condensing atmospheric environment of < 40 °C and 90%RH. The module is rated at the moisture sensitivity level (MSL) of 3.

After unpacking, the module must be soldered within 168 hours with the factory conditions 25 ± 5 °C and 60 %RH. If the above conditions are not met, the module needs to be baked.

11.2 Electrostatic Discharge (ESD)

- Human body model (HBM): ±2000 V
- Charged-device model (CDM): ±500 V

11.3 Reflow Profile

Solder the module in a single reflow.





11.4 Ultrasonic Vibration

Avoid exposing Espressif modules to vibration from ultrasonic equipment, such as ultrasonic welders or ultrasonic cleaners. This vibration may induce resonance in the in-module crystal and lead to its malfunction or even failure. As a consequence, **the module may stop working or its performance may deteriorate**.

Related Documentation and Resources

Related Documentation

- ESP32 Series Datasheet Specifications of the ESP32 hardware.
- ESP32 Technical Reference Manual Detailed information on how to use the ESP32 memory and peripherals.
- ESP32 Hardware Design Guidelines Guidelines on how to integrate the ESP32 into your hardware product.
- ESP32 ECO and Workarounds for Bugs Correction of ESP32 design errors.
- ESP32 Series SoC Errata Descriptions of known errors in ESP32 series of SoCs.
- Certificates
 <u>https://espressif.com/en/support/documents/certificates</u>
- ESP32 Product/Process Change Notifications (PCN) https://espressif.com/en/support/documents/pcns
- ESP32 Advisories Information on security, bugs, compatibility, component reliability. https://espressif.com/en/support/documents/advisories
- Documentation Updates and Update Notification Subscription
 https://espressif.com/en/support/download/documents

Developer Zone

- ESP-IDF Programming Guide for ESP32 Extensive documentation for the ESP-IDF development framework.
- ESP-IDF and other development frameworks on GitHub.
 <u>https://github.com/espressif</u>
- ESP32 BBS Forum Engineer-to-Engineer (E2E) Community for Espressif products where you can post questions, share knowledge, explore ideas, and help solve problems with fellow engineers. https://esp32.com/
- The ESP Journal Best Practices, Articles, and Notes from Espressif folks. https://blog.espressif.com/
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Revision History

Date	Version	Release notes
2025-04-14	v2.1	Added notes about erase cycles and retention time for flash in Table 2 ESP32- WROVER-IB Series Comparison
2023-02-09	v2.0	 Major updates: Removed contents about hall sensor according to <u>PCN20221202</u> Other updates: Added source files of PCB land patterns and 3D models of the modules (if available) in Section 9: <i>Recommended PCB Land Pattern</i>
2022-09-22	v1.9	 Replaced the ordering information table with Table 1 and 2 Added information about the setup and hold times for the strapping pins in Section 2.3 Added ESP32-WROVER-IB dimension figure 7 Added Chapter 11
2022-03-04	v1.8	Updated Ordering Information Table Added a link to RF certificates in Table 3 Updated Table 7 Added a note below Figure 6 Updated the description to the connector Added Section 11.4:
2021-08-10	v1.7	Added ESP32-WROVER-IB module Added Figure 4: Schematics of ESP32-WROVER-IB Updated Figure 1: Pin Layout (Top View), Figure 3: Schematics of ESP32- WROVER-B, and Figure 5: Peripheral Schematics Replaced Espressif Product Ordering Information with ESP Product Selector Updated the description of TWAI in Table 3: Overview Added a label of (Not Recommended For New Designs) to this document
2021-02-09	V1.6	Updated Figure 6: <i>ESP32-WROVER-B Physical Dimensions</i> and Figure 8: <i>Recommended PCB Land Pattern</i> Deleted Reset Circuit and Discharge Circuit for VDD33 Rail in Section 7: <i>Peripheral Schematics</i> Modified the note below Figure Reflow Profile. Updated the trade mark from TWAI [™] to TWAI [®] . Added TWAI TM in Table 3;
2020-11-27	V1.5	Updated the C value in RC circuit from 0.1 μ F to 1 μ F.
2020-03-13	V1.4	 Changed the module's operating temperature range from -40°C ~ 65°C to -40°C ~ 85°C Added documentation feedback link

Date	Version	Release notes
2019.09	V1.3	 Changed the supply voltage range from 2.7 V ~ 3.6 V to 3.0 V ~ 3.6 V; Added Moisture sensitivity level (MSL) 3 in Table 3 <i>ESP32-WROVER-B Specifications</i>; Added notes about "Operating frequency range" and "TX power" under Table 10 <i>Wi-Fi Radio Characteristics</i>; Updated Section 7 <i>Peripheral Schematics</i> and added a note about RC delay circuit under it; Updated Figure 9 <i>Recommended PCB Land Pattern</i>.
2019.01	V1.2	Changed the RF power control range in Table 12 from $-12 \sim +12$ to $-12 \sim +9$ dBm.
2018.10	V1.1	Added notes on module custom options to Ordering Information Table; Added "Cumulative IO output current" entry to Table 7: Absolute Maximum Rat- ings; Added more parameters to Table 9: DC Characteristics.
2018.07	V1.0	 Official release: Added certifications and reliability test items the module has passed in Table 3: ESP32-WROVER-B Specifications; Updated the dimensions of the module; Changed the module's recommended operating temperature from -40°C ~ 85°C to -40°C ~ 65°C; Updated table 10: Wi-Fi Radio.
2018.06	V0.1	Preliminary release.



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